

L Number	Hits	Search Text	DB	Time stamp
1	10575	mixed adj2 oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/05 15:18
8	7645	doped adj2 oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/05 15:18
15	13425	doped near3 oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/05 15:19
22	16563	(dopant doped doping) near3 (oxide "Al.sub.2" adj "O.sub.3")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/05 15:20
29	53032	(dopant doped doping mixed) near5 (oxide "Al.sub.2" adj "O.sub.3")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/05 15:43
36	184465	(substrate deposit\$3 sputter\$4 cosputter\$4) near12 ("25.degree." "25" ((ambient room) adj (temperature temp)) "20.degree." "20")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/05 16:02
43	3514	((silicon adj monoxide) or SiO) near15 (sputter\$4 evaporat\$3 cosputter\$4 coevaporat\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/05 15:24
50	9169	((("Al.sub.2" adj "O.sub.3") or Al2O3 or alumina or sapphire) with (source target)) or ((aluminum adj oxide) with (source target))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/05 15:44
57	12	((silicon adj monoxide) or SiO) near15 (sputter\$4 evaporat\$3 cosputter\$4 coevaporat\$3)) same (((("Al.sub.2" adj "O.sub.3") or Al2O3 or alumina or sapphire) with (source target)) or ((aluminum adj oxide) with (source target)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/05 15:34
64	12349	((dopant doped doping mixed) near5 (oxide "Al.sub.2" adj "O.sub.3")) same (silicon or Si)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/05 15:42
71	37	((silicon adj monoxide) or SiO) near15 (sputter\$4 evaporat\$3 cosputter\$4 coevaporat\$3)) and (((dopant doped doping mixed) near5 (oxide "Al.sub.2" adj "O.sub.3")) same (silicon or Si))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/05 15:35
78	8632	((dopant doped doping mixed) near5 (oxide "Al.sub.2" adj "O.sub.3")) near15 (silicon or Si)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/05 15:43

85	2534	((substrate deposit\$3 sputter\$4 cosputter\$4) near12 ("25.degree." "25" ((ambient room) adj (temperature temp)) "20.degree." "20")) and (((dopant doped doping mixed) near5 (oxide "Al.sub.2" adj "O.sub.3")) near15 (silicon or Si))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/05 15:43
99	7572	(Si silicon) near5 (dopant doped doping mixed) near5 (oxide "Al.sub.2" adj "O.sub.3")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/05 15:44
106	1554	(Si or silicon) near10 (dopant doped doping mixed) near10 (("Al.sub.2" adj "O.sub.3") or Al2O3 or alumina or (aluminum adj oxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/05 15:46
113	176	((substrate deposit\$3 sputter\$4 cosputter\$4) near12 ("25.degree." "25" ((ambient room) adj (temperature temp)) "20.degree." "20")) and ((Si or silicon) near10 (dopant doped doping mixed) near10 (("Al.sub.2" adj "O.sub.3") or Al2O3 or alumina or (aluminum adj oxide)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/05 15:46
120	8	((substrate deposit\$3 sputter\$4 cosputter\$4) near12 ("25.degree." "25" ((ambient room) adj (temperature temp)) "20.degree." "20")) same ((Si or silicon) near10 (dopant doped doping mixed) near10 (("Al.sub.2" adj "O.sub.3") or Al2O3 or alumina or (aluminum adj oxide)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/05 15:46
92	328	((substrate deposit\$3 sputter\$4 cosputter\$4) near12 ("25.degree." "25" ((ambient room) adj (temperature temp)) "20.degree." "20")) same (((dopant doped doping mixed) near5 (oxide "Al.sub.2" adj "O.sub.3")) near15 (silicon or Si))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/05 15:47
127	20636	(substrate deposit\$3 sputter\$4 cosputter\$4) near12 ("25.degree." ((ambient room) adj (temperature temp)) "20.degree."))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/05 16:01
141	0	((Si or silicon) near10 (dopant doped doping mixed) near10 (("Al.sub.2" adj "O.sub.3") or Al2O3 or alumina or (aluminum adj oxide))) same ((substrate deposit\$3 sputter\$4 cosputter\$4) near12 ("25.degree." ((ambient room) adj (temperature temp)) "20.degree."))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/05 15:48
134	41	((Si or silicon) near10 (dopant doped doping mixed) near10 (("Al.sub.2" adj "O.sub.3") or Al2O3 or alumina or (aluminum adj oxide))) and ((substrate deposit\$3 sputter\$4 cosputter\$4) near12 ("25.degree." ((ambient room) adj (temperature temp)) "20.degree."))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/05 15:48
148	1	((substrate deposit\$3 sputter\$4 cosputter\$4) near12 ("25.degree." ((ambient room) adj (temperature temp)) "20.degree.")) near20 (thermal adj budget)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/05 15:56
155	589	(cool\$4 near3 (substrate wafer)) near20 ((substrate deposit\$3 sputter\$4 cosputter\$4) near12 ("25.degree." ((ambient room) adj (temperature temp)) "20.degree."))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/05 16:01
162	34	((dopant doped doping mixed) near5 (oxide "Al.sub.2" adj "O.sub.3")) and ((cool\$4 near3 (substrate wafer)) near20 ((substrate deposit\$3 sputter\$4 cosputter\$4) near12 ("25.degree." ((ambient room) adj (temperature temp)) "20.degree.")))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/05 15:57
169	3	((cool\$4 near3 (substrate wafer)) near20 ((substrate deposit\$3 sputter\$4 cosputter\$4) near12 ("25.degree." ((ambient room) adj (temperature temp)) "20.degree."))) and (applied adj materials).asn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/05 16:03

176	70836	(deposit\$3 sputter\$4 cosputter\$4) near12 ("25.degree." "25" ((ambient room) adj (temperature temp)) "20.degree." "20")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/05 16:07
183	717	((deposit\$3 sputter\$4 cosputter\$4) near12 ("25.degree." "25" ((ambient room) adj (temperature temp)) "20.degree." "20")) and (applied adj materials).asn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/05 16:05
190	76	((deposit\$3 sputter\$4 cosputter\$4) near12 ("25.degree." "25" ((ambient room) adj (temperature temp)) "20.degree." "20")) and (applied adj materials).asn.) and ((dopant doped doping mixed) near5 (oxide "Al.sub.2" adj "O.sub.3"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/05 16:05
197	107	((substrate deposit\$3 sputter\$4 cosputter\$4) near12 ("25.degree." ((ambient room) adj (temperature temp)) "20.degree.")) and (applied adj materials).asn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/05 16:05
204	18	((substrate deposit\$3 sputter\$4 cosputter\$4) near12 ("25.degree." ((ambient room) adj (temperature temp)) "20.degree.")) and (applied adj materials).asn.) and ((dopant doped doping mixed) near5 (oxide "Al.sub.2" adj "O.sub.3"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/05 16:05
211	1224	(sputter\$4 cosputter\$4) near12 ("25.degree." ((ambient room) adj (temperature temp)) "20.degree.")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/05 16:07
218	56	((sputter\$4 cosputter\$4) near12 ("25.degree." ((ambient room) adj (temperature temp)) "20.degree.")) near20 (necessary conventional conventionally typical essential beneficial beneficially typically)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/05 16:09